REVISIONS			
LTR	DESCRIPTION	DATE (YR-MO-DA)	APPROVED
A	Update drawing to reference MIL-STD-1835. Made the following changes to table I: Output low voltage, changed I_{OL} from -1.6 mA to 1.6 mA; interrupt pulse width, PW_{IRQ}, changed unit from ns to t_{cyc}; conversion time, changed max limit from (t_{cyc} + 32000) to (t_{cyc} + 40000); delay time, t_{ASED}, changed min limit from 105.5 to 95.5. Modified figure 1, case outline Y. Editorial changes throughout.	92-12-04	Monica L. Poelking
B	Update boilerplate to the requirements of MIL-PRF-38535. Editorial changes throughout. - TVN	02-02-15	Thomas M. Hess
C	Update boilerplate to current MIL-PRF-38535 requirements. - CFS	08-01-09	Thomas M. Hess

REV																				
SHEET																				
REV	C	C	C	C	C	C	C	C	C	C	C	C	C	C	C	C	C	C	C	C
SHEET	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	32	33	34

REV STATUS OF SHEETS	REV	C	C	C	C	C	C	C	C	C	C	C	C	C	C
	SHEET	1	2	3	4	5	6	7	8	9	10	11	12	13	14

PMIC N/A

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DRAWING APPROVAL DATE
90-10-11

REVISION LEVEL
C

DEFENSE SUPPLY CENTER COLUMBUS
COLUMBUS, OHIO 43218-3990
http://www.dscc.dla.mil

STANDARD MICROCIRCUIT DRAWING

THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS AND AGENCIES OF THE DEPARTMENT OF DEFENSE

AMSC N/A

MICROCIRCUIT, DIGITAL, HIGH SPEED CMOS, 8-BIT MICROCONTROLLER, MONOLITHIC SILICON

SIZE	CAGE CODE	
A	**67268**	**5962-89527**

SHEET 1 OF 34

1. SCOPE

1.1 Scope. This drawing describes device requirements for MIL-STD-883 compliant, non-JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A.

1.2 Part or Identifying Number (PIN). The complete PIN is as shown in the following example:

5962-89527	01	X	X
Drawing number	Device type (see 1.2.1)	Case outline (see 1.2.2)	Lead finish (see 1.2.3)

1.2.1 Device type(s). The device type(s) identify the circuit function as follows:

Device type	Generic number	Circuit function
01	68HC811E2	8-bit microcontroller, EEPROM 2K bytes, RAM 256 bytes

1.2.2 Case outline(s). The case outline(s) are as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	Terminals	Package style
X	GDIP1-T48 or CDIP2-T48	48	Dual-in-line
Y	See figure 1	52	Square leaded chip carrier

1.2.3 Lead finish. The lead finish is as specified in MIL-PRF-38535, appendix A.

1.3 Absolute maximum ratings.

Supply voltage range	-0.3 V dc to +7.0 V dc
Storage temperature range	-65°C to +150°C
Maximum power dissipation (P_D)	1.75 W
Lead temperature (soldering, 5 seconds)	+270°C
Junction temperature (T_J)	+150°C
Thermal resistance, junction to case (θ_{JC}):	See MIL-STD-1835

1.4 Recommended operating conditions.

Supply voltage range (V_{DD})	4.5 V dc minimum to 5.5 V dc maximum
High level input voltage (V_{IH})	$0.8V_{DD}$ V dc
Low level input voltage range (V_{IL})	V_{SS} to $0.2V_{DD}$ V dc
Maximum high level output voltage (V_{OH})	V_{DD} - 0.1 V dc
Maximum low level output voltage (V_{OL})	0.4 V dc
Case operating temperature range (T_C)	-55°C to +125°C
Frequency of operation	DC to 2.1 MHz

2. APPLICABLE DOCUMENTS

2.1 Government specification, standards, and handbooks. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883 - Test Method Standard Microcircuits.
MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings.
MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at http://assist.daps.dla.mil/quicksearch/ or http://assist.daps.dla.mil or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 Item requirements. The individual item requirements shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein. Product built to this drawing that is produced by a Qualified Manufacturer Listing (QML) certified and qualified manufacturer or a manufacturer who has been granted transitional certification to MIL-PRF-38535 may be processed as QML product in accordance with the manufacturers approved program plan and qualifying activity approval in accordance with MIL-PRF-38535. This QML flow as documented in the Quality Management (QM) plan may make modifications to the requirements herein. These modifications shall not affect form, fit, or function of the device. These modifications shall not affect the PIN as described herein. A "Q" or "QML" certification mark in accordance with MIL-PRF-38535 is required to identify when the QML flow option is used.

3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535, appendix A and herein.

3.2.1 Case outlines. The case outlines shall be in accordance with 1.2.2 herein and on figure 1.

3.2.2 Terminal connections. The terminal connections shall be as specified on figure 2.

3.2.3 Block diagram. The block diagram shall be as specified on figure 3.

3.2.4 Test circuit and switching waveforms. The test circuit and switching waveforms shall be as specified on figure 4.

3.3 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in table I and shall apply over the full case operating temperature range.

3.4 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are described in table I.

3.5 Marking. Marking shall be in accordance with MIL-PRF-38535, appendix A. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device.

3.5.1 Certification/compliance mark. A compliance indicator “C” shall be marked on all non-JAN devices built in compliance to MIL-PRF-38535, appendix A. The compliance indicator “C” shall be replaced with a “Q” or “QML” certification mark in accordance with MIL-PRF-38535 to identify when the QML flow option is used.

3.6 Certificate of compliance. A certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.7 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply shall affirm that the manufacturer's product meets the requirements of MIL-PRF-38535, appendix A and the requirements herein.

3.7 Certificate of conformance. A certificate of conformance as required in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.

3.8 Notification of change. Notification of change to DSCC-VA shall be required for any change that affects this drawing.

3.9 Verification and review. DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

3.10 Processing EEPROMS. All testing requirements and quality assurance provisions herein shall be satisfied by the manufacturer prior to delivery.

3.10.1 Erasure of EEPROM. When specified, devices shall be erased in accordance with the procedures and characteristics specified in 4.4.

3.10.2 Programmability of EEPROM. When specified, devices shall be programmed to the specified pattern using the procedures and characteristics specified in 4.5.

3.10.3 Verification of erasure or programmability of EEPROM. When specified, devices shall be verified as either programmed to the specified pattern or erased. As a minimum, verification shall consist of performing a functional test (subgroup 7) to verify that all bits are in the proper state. Any bit that does not verify to be in the proper state shall constitute a device failure, and shall be removed from the lot.

TABLE I. Electrical performance characteristics.

Test		Symbol	Conditions $+4.5\ V \le V_{DD} \le +5.5\ V$ $V_{SS} = 0\ V\ dc$ $-55°C \le T_C \le +125°C$	Group A subgroups	Limits		Unit
					Min	Max	
Output high voltage; all outputs except $\overline{RESET}$, XTAL, and MODA		V_{OH}	$I_{OH} = -0.8\ mA$ $V_{DD} = 4.5\ V$ 1/	1, 2, 3	V_{DD}-0.8		V
Output low voltage; all outputs except XTAL		V_{OL}	$I_{OL} = 1.6\ mA$ $V_{DD} = 4.5\ V$	1, 2, 3		0.4	V
Input high voltage	All inputs except $\overline{RESET}$	V_{IH}	$V_{DD} = 4.5\ V$	1, 2, 3	$0.7V_{DD}$	V_{DD}	V
	$\overline{RESET}$				$0.8V_{DD}$	V_{DD}	
Input low voltage; all inputs		V_{IL}	$V_{DD} = 4.5\ V$	1, 2, 3	V_{SS}	$0.2V_{DD}$	V
I/O port, three-state leakage, PA3, PA7, PC0-PC7, PD0-PD5, AS/STRA, MODA/$\overline{LIR}$, $\overline{RESET}$		I_{OZ}	$V_{DD} = 5.5\ V$ $V_{IN} = V_{IH}$ or V_{IL}	1, 2, 3		±10	µA
Input current	PA0-PA2, $\overline{IRQ}$, $\overline{XIRQ}$	I_{IN}	$V_{DD} = 5.5\ V$ $V_{IN} = V_{DD}$ or V_{SS} 2/	1, 2, 3		±1	µA
	MODB/V_{stby}					±10	
RAM standby voltage powerdown		V_{SB}		1, 2, 3	4.0	V_{DD}	V
RAM standby current powerdown		I_{SB}		1, 2, 3		20	µA
Total supply current 3/	RUN:	I_{DD}	$V_{DD} = 5.5\ V$ Single chip	1, 2, 3		20	mA
			$V_{DD} = 5.5\ V$ Expanded multiplexed			30	
	WAIT: All peripheral functions shut down	WI_{DD}	$V_{DD} = 5.5\ V$ Single chip	1, 2, 3		10	mA
			$V_{DD} = 5.5\ V$ Expanded multiplexed			15	
	STOP: No clocks	SI_{DD}	$V_{DD} = 5.5\ V$ Single chip	1, 2, 3		300	µA
Input capacitance	PA0-PA2, PE0-PE7, EXTAL, $\overline{IRQ}$, $\overline{XIRQ}$	C_{IN}	$V_{IN} = 0\ V$ $f_{IN} = 1\ MHz$ See 4.3.1b	4		8	pF
	PA7, PA3, PC0-PC7, PD0-PD5, AS/STRA, MODA/$\overline{LIR}$, $\overline{RESET}$					14	
Functional test			$V_{DD} = 4.5\ V, 5.5\ V$	7, 8			

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test		Symbol	Conditions +4.5 V ≤ V_{DD} ≤ +5.5 V V_{SS} = 0 V dc -55°C ≤ T_C ≤ +125°C		Group A subgroups	Limits		Unit
						Min	Max	
Control timing								
Frequency of operation		f_o	V_{DD} = 4.5 V See figure 4.	1.0 MHz	9, 10, 11	0	1.0	MHz
				2.1 MHz		0	2.1	
E clock period		t_{cyc}		1.0 MHz	9, 10, 11	1000.0		ns
				2.1 MHz		476.0		
Crystal frequency		f_{XTAL}		1.0 MHz	9, 10, 11		4.0	MHz
				2.1 MHz			8.4	
External oscillator frequency		f_{OEX}		1.0 MHz	9, 10, 11	0	4.0	MHz
				2.1 MHz		0	8.4	
Processor control setup		t_{PCS}		1.0 MHz	9, 10, 11	200.0		ns
				2.1 MHz		69.0		
Reset input pulse width	To guarantee external reset vector 4/	PW_{RSTL}		1.0 MHz	9, 10, 11	8.0		t_{cyc}
				2.1 MHz		8.0		
	Minimum input time may be preempted by internal reset			1.0 MHz	9, 10, 11	1.0		
				2.1 MHz		1.0		
Mode programming setup time		t_{MPS}		1.0 MHz	9, 10, 11	2.0		t_{cyc}
				2.1 MHz		2.0		
Mode programming hold time		t_{MPH}		1.0 MHz	9, 10, 11	0.0		ns
				2.1 MHz		0.0		
Interrupt pulse width $\overline{IRQ}$ edge sensitive mode		PW_{IRQ}		1.0 MHz	9, 10, 11	2.0		t_{cyc}
				2.1 MHz		2.0		
Wait recovery startup time		t_{WRS}		1.0 MHz	9, 10, 11		4.0	t_{cyc}
				2.1 MHz			4.0	
Timer pulse width input capture, pulse accumulator input		PW_{TIM}		1.0 MHz	9, 10, 11	1020.0		ns
				2.1 MHz		496.0		

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test		Symbol	Conditions +4.5 V ≤ V_{DD} ≤ +5.5 V V_{SS} = 0 V dc -55°C ≤ T_C ≤ +125°C		Group A subgroups	Limits		Unit
						Min	Max	
Peripheral port timing 5/								
Frequency of operation (E clock frequency)		f_o	V_{DD} = 4.5 V See figure 4	1.0 MHz	9, 10, 11	1.0	1.0	MHz
				2.1 MHz		2.1	2.1	
E clock period		t_{cyc}		1.0 MHz	9, 10, 11	1000.0		ns
				2.1 MHz		476.0		
Peripheral data setup time MCU read of ports A, C, D, and E		t_{PDSU}		1.0 MHz	9, 10, 11	100.0		ns
				2.1 MHz		100.0		
Peripheral data hold time MCU read of ports A, C, D, and E		t_{PDH}		1.0 MHz	9, 10, 11	50.0		ns
				2.1 MHz		50.0		
Delay time, peripheral data write	MCU write to port A	t_{PWD}		1.0 MHz	9, 10, 11		175.0	ns
				2.1 MHz			175.0	
	MCU write to port B, C, and D			1.0 MHz	9, 10, 11		340.0	
				2.1 MHz			209.0	
Input data setup time (port C)		t_{IS}		1.0 MHz	9, 10, 11	60.0		ns
				2.1 MHz		60.0		
Input data hold time (port C)		t_{IH}		1.0 MHz	9, 10, 11	100.0		ns
				2.1 MHz		100.0		
Delay time, E fall to STRB		t_{DEB}		1.0 MHz	9, 10, 11		350.0	ns
				2.1 MHz			219.0	
Setup time, STRA asserted to E fall 6/		t_{AES}		1.0 MHz	9, 10, 11	0.0		ns
				2.1 MHz		0.0		
Delay time, STRA asserted to port C, data output valid		t_{PCD}		1.0 MHz	9, 10, 11		100.0	ns
				2.1 MHz			100.0	
Hold time, STRA negated to port C data		t_{PCH}		1.0 MHz	9, 10, 11	10.0		ns
				2.1 MHz		10.0		
Three-state hold time		t_{PCZ}		1.0 MHz	9, 10, 11		150.0	ns
				2.1 MHz			150.0	

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test		Symbol	Conditions $+4.5\ V \le V_{DD} \le +5.5\ V$ $V_{SS} = 0\ V\ dc$ $-55°C \le T_C \le +125°C$ $750\ KHz \le E \le 2.1\ MHz$	Group A subgroups	Limits		Unit
					Min	Max	
A/D converter							
Resolution		RES	Number of bits resolved by the A/D	4, 5, 6	8		Bits
Non-linearity		NLI	Maximum deviation from the ideal and A/D transfer characteristics	4, 5, 6		±1/2	LSB
Zero error		ZER	Diffference between the output of an ideal and an actual A/D for zero input voltage	4, 5, 6		±1/2	LSB
Full-scale error		FSE	Diffference between the output of an ideal and an actual A/D for full-scale input voltage	4, 5, 6		±1/2	LSB
Total unadjusted error		TUE	Maximum sum of non-linearity, zero error, and full-scale error	4, 5, 6		±1/2	LSB
Quantization error		QTE	Uncertainty due to converter resolution	4, 5, 6		±1/2	LSB
Absolute accuracy		AAC	Difference between the actual input voltage and the full-scale weighted equivalent of the binary output code, all error sources included	4, 5, 6		±1	LSB
Conversion range		COR	Analog input voltage range	4, 5, 6	V_{RL}	V_{RH}	V
Maximum analog reference voltage		V_{RH}	7/	4, 5, 6	V_{RL}	V_{DD}+0.1	V
Minimum analog reference voltage		V_{RL}	7/	4, 5, 6	V_{SS}-0.1	V_{RH}	V
Minimum difference between V_{RH} and V_{RL}		ΔV_R	7/	4, 5, 6	3		V
Conversion time	E clock	CONT	Total time to perform a single analog-to-digital conversion	4, 5, 6		32 8/	t_{cyc}
	Internal RC oscillator 8/					t_{cyc} +40000	ns
Monotonicity		MON	Conversion result never decreases with an increase in input voltage and has no missing codes 9/	4, 5, 6			
Zero input reading		ZIR	Conversion result when $V_{IN} = V_{RL}$	4, 5, 6	00		Hex
Full scale reading		FSR	Conversion result when $V_{IN} = V_{RH}$	4, 5, 6		FF	Hex
Sample acquisition time	E clock 10/	SAT	Analog input acquisition sampling time	4, 5, 6	12		t_{cyc}
	Internal RC oscillator 11/					12	µs
Input leakage	PE0-PE7	I_{IN}	Input leakage on A/D pins	9, 10, 11		400	nA
	V_{RL}, V_{RH}					1.0	µA

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test	Symbol	Conditions $+4.5\ V \le V_{DD} \le +5.5\ V$ $V_{SS} = 0\ V\ dc$ $-55°C \le T_C \le +125°C$		Group A subgroups	Limits		Unit
					Min	Max	
Expansion bus timing							
Frequency of operation (E clock frequency)	f_o	$V_{DD} = 4.5\ V$ See figure 4	1.0 MHz	9, 10, 11	1.0	1.0	MHz
			2.1 MHz		2.1	2.1	
Cycle time	t_{cyc}		1.0 MHz	9, 10, 11	1000.0		ns
			2.1 MHz		476.0		
Pulse width, E low	PW_{EL}		1.0 MHz	9, 10, 11	477.0		ns
			2.1 MHz		215.0		
Pulse width, E high	PW_{EH}		1.0 MHz	9, 10, 11	472.0		ns
			2.1 MHz		210.0		
E and AS rise time	t_r		1.0 MHz	9, 10, 11		20.0	ns
			2.1 MHz			20.0	
E and AS fall time	t_f		1.0 MHz	9, 10, 11		20.0	ns
			2.1 MHz			20.0	
Address hold time	t_{AH}		1.0 MHz	9, 10, 11	95.5		ns
			2.1 MHz		30.0		
Non-muxed address valid time to E rise 8/	t_{AV}		1.0 MHz	9, 10, 11	281.5		ns
			2.1 MHz		85.0		
Read data setup time	t_{DSR}		1.0 MHz	9, 10, 11	30.0		ns
			2.1 MHz		30.0		
Read data hold time	t_{DHR}		1.0 MHz	9, 10, 11	10.0	145.5	ns
			2.1 MHz		10.0	80.0	
Write data delay time 8a/	t_{DDW}		1.0 MHz	9, 10, 11		190.5	ns
			2.1 MHz			125.0	
Write data hold time 8a/	t_{DHW}		1.0 MHz	9, 10, 11	95.5		ns
			2.1 MHz		30.0		
Muxed address valid time to E rise 8b/	t_{AVM}		1.0 MHz	9, 10, 11	271.5		ns
			2.1 MHz		75.0		
Muxed address valid time to AS fall	t_{ASL}		1.0 MHz	9, 10, 11	151.0		ns
			2.1 MHz		20.0		
Muxed address hold time 8b/	t_{AHL}		1.0 MHz	9, 10, 11	95.5		ns
			2.1 MHz		30.0		

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test		Symbol	Conditions +4.5 V ≤ V_{DD} ≤ +5.5 V V_{SS} = 0 V dc -55°C ≤ T_C ≤ +125°C		Group A subgroups	Limits		Unit
						Min	Max	
Expansion bus timing - Continued								
Delay time, E to AS rise 8b/		t_{ASD}	V_{DD} = 4.5 V See figure 4	1.0 MHz	9, 10, 11	115.5		ns
				2.1 MHz		50.0		
Pulse width, AS high		PW_{ASH}		1.0 MHz	9, 10, 11	221.0		ns
				2.1 MHz		90.0		
Delay time, AS to E rise 8b/		t_{ASED}		1.0 MHz	9, 10, 11	95.5		ns
				2.1 MHz		40.0		
MPU address access time 8b/		t_{ACCA}		1.0 MHz	9, 10, 11	733.5		ns
				2.1 MHz		275.0		
MPU access time		t_{ACCE}		1.0 MHz	9, 10, 11		442.0	ns
				2.1 MHz			180.0	
Muxed address delay (previous cycle MPU read) 8a/		t_{MAD}		1.0 MHz	9, 10, 11	145.5		ns
				2.1 MHz		80.0		
Serial peripheral interface (SPI) timing								
Operating frequency	Master	$f_{op(m)}$	V_{DD} = 4.5 V See figure 4		9, 10, 11	0	0.5	MHz
	Slave	$f_{op(s)}$				0	2.1	
Cycle time	Master	$t_{cyc(m)}$			9, 10, 11	2.0		t_{cyc}
	Slave	$t_{cyc(s)}$				480		ns
Enable lead time	Master	$t_{lead(m)}$			9, 10, 11	12/		ns
	Slave	$t_{lead(s)}$				240		
Enable lag time	Master	$t_{lag(m)}$			9, 10, 11	12/		ns
	Slave	$t_{lag(s)}$				240		
Clock (SCK) high time	Master	$t_{w(SCKH)m}$			9, 10, 11	340		ns
	Slave	$t_{w(SCKH)s}$				190		
Clock (SCK) low time	Master	$t_{w(SCKL)m}$			9, 10, 11	340		ns
	Slave	$t_{w(SCKL)s}$				190		
Data setup time	Master	$t_{su(m)}$			9, 10, 11	100		ns
	Slave	$t_{su(s)}$				100		
Data hold time	Master	$t_{h(m)}$			9, 10, 11	100		ns
	Slave	$t_{h(s)}$				100		

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test		Symbol	Conditions +4.5 V ≤ V_{DD} ≤ +5.5 V V_{SS} = 0 V dc -55°C ≤ T_C ≤ +125°C		Group A subgroups	Limits		Unit
						Min	Max	
Serial peripheral interface (SPI) timing – Continued								
Access time (time to data active from high-impedance state) slave		t_a	V_{DD} = 4.5 V See figure 4		9, 10, 11	0	120	ns
Disable time (hold time to high-impedance state) slave		t_{dis}			9, 10, 11		240	ns
Data valid (after enable edge) 13/		$t_{v(s)}$			9, 10, 11		240	ns
Data hold time (outputs, after enable edge)		t_{ho}			9, 10, 11	0		ns
Rise time 9/	SCK, MOSI, and MISO	t_{rm}	V_{DD} = 4.5 V See figure 4	20% V_{DD} to 70% V_{DD} C_L = 200 pF	9, 10, 11		100	ns
	SCK, MOSI, MISO, and $\overline{SS}$	t_{rs}					2.0	µs
Fall time 9/	SCK, MOSI, and MISO	t_{fm}		70% V_{DD} to 20% V_{DD} C_L = 200 pF	9, 10, 11		100	ns
	SCK, MOSI, MISO, and $\overline{SS}$	t_{fs}					2.0	µs
Programming time	2.1 MHz 14/		V_{DD} = 4.5 V Not shown		9, 10, 11	25		ms
	RC oscillator enabled 15/					25		
Erase time, byte, row, and bulk					9, 10, 11	25		ms
Write/erase endurance						5000		cycles
Data retention 16/						10		years

1/ V_{OH} specification for $\overline{RESET}$ and MODA is not applicable because they are open-drain pins. V_{OH} specification not applicable to ports C and D in wire-OR mode.
2/ See A/D specification for leakage current for port E.
3/ All ports configured as inuts, $V_{IL} \le 0.2$ V, $V_{IH} \ge V_{DD} - 0.2$ V, no dc loads, EXTAL driven with a square wave, and t_{cyc} = 476.5 ns.
4/ $\overline{RESET}$ will be recognized during the first clock cycle it is held low. Internal circuitry then drives the pin low for four clock cycles, releases the pin, and samples the pin level two cycles later to determine the source of the interrupt.
5/ Ports C and D timing is valid for active drive (CWOM and DWOM bits not set in PIOC and SPCR registers, respectively).
6/ If this setup time is met, STRB will acknowledge in the next cycle. If it is not met, the response may be delayed one more cycle.
7/ Performance verified down to 2.5 V ΔR, but accuracy is tested and guaranteed at ΔR = 5 V ±10 percent. Source impedances greater than 10 KΩ will adversely affect accuracy, due mainly to input leakage.
8/ Input clocks with duty cycles other than 50 percent will affect bus performance. Timing parameters affected by input clock duty cycle are identified by "a" and "b". To recalculate the approximate bus timing values, substitute the following expressions in place of 1/8 t_{cyc} in the above formulas where applicable:
   a. (1 - dc) x (1/4 x t_{cyc})
   b. DC x (1/4 x t_{cyc})
   Where dc is the decimal value of duty cycle percentage (high time).
9/ Subgroups 4, 5, and 6 shall be guaranteed for all bits.
10/ Absolute (shall be exact value).

TABLE I. Electrical performance characteristics - Continued.

11/ Conversions using internal RC oscillator not tested at -55°C.
12/ Signal production depends on software.
13/ Assumes 200 pF load on all SPI pins.
14/ Programming time tested at 2.1 MHz with internal RC oscillator disabled for all three temperatures.
15/ Programming time with internal RC oscillator enabled is tested at 500 KHz. Recommend that internal RC oscillator be used when frequency falls below 1.0 MHz or when temperature exceeds 85°C and frequency falls below 2.0 MHz.
16/ The 10 years specified is based on an average operating temperature of 70°C.

Case Y

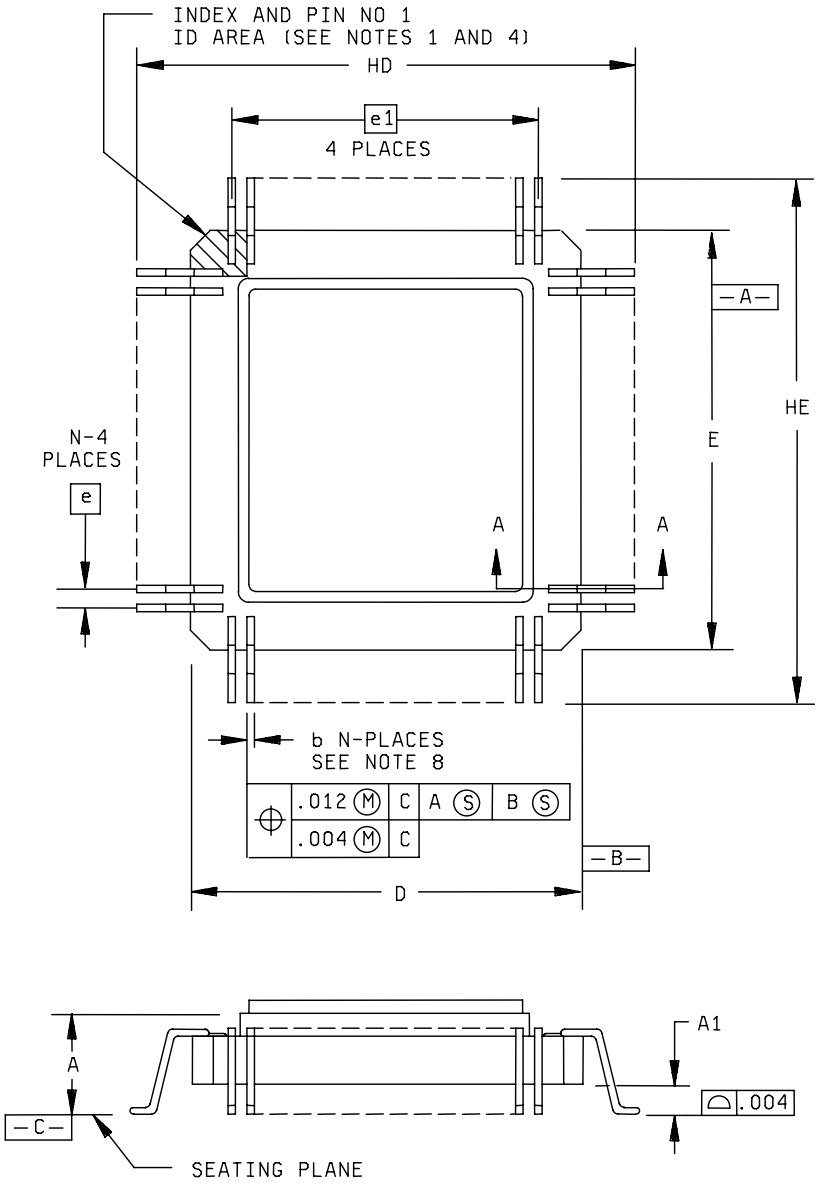
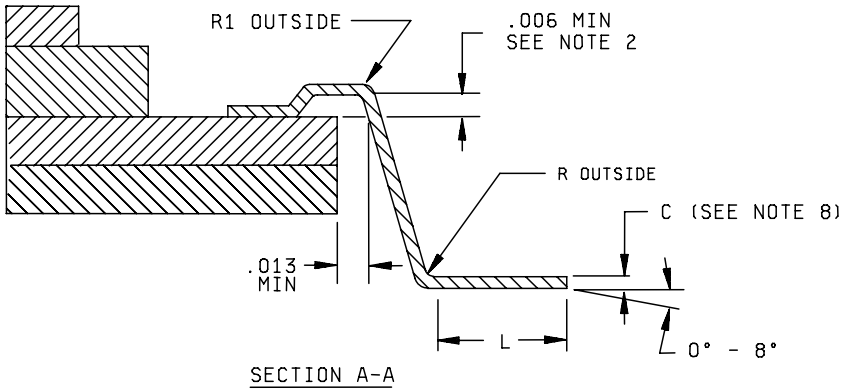


FIGURE 1. Case Outline.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43218-3990	SIZE A		5962-89527
		REVISION LEVEL C	SHEET 13



Symbol	Inches		Millimeters	
	Min	Max	Min	Max
A		.125		3.175
A1	.018	.035	0.457	0.889
b	.018	.030	0.457	0.762
c	.005	.010	0.127	0.254
D/E	.940	.960	23.88	24.38
e	.050 BSC		1.27 BSC	
e1	.600 BSC		15.24 BSC	
HD/HE	1.133	1.147	28.78	29.13
L	.024	.040	0.610	1.016
N	52		52	
R	.011	.034	0.279	0.864
R1	.009		0.229	

NOTES:
1. A terminal 1 identification mark shall be located at the index corner in the shaded area shown. Terminal 1 is located immediately adjacent to and counterclockwise from the index corner. Terminal numbers increase in a counterclockwise direction when viewed as shown.
2. Generic lead attach dogleg depiction.
3. Dimension N: Number of terminals.
4. Corner shapes (square, notch, radius, etc.) may vary from that shown on the drawing. The index corner shall be clearly unique.
5. Metric equivalents are given for general information only.
6. Controlling dimension: Inch.
7. Datums X and Y to be determined where center leads exit the body.
8. Dimensions b and c include lead finish.

FIGURE 1. Case Outline - Continued.

Device type	01		
Case outline	X		
Terminal number	Terminal symbol	Terminal number	Terminal symbol
1	PA7/PAI/OC1	25	MODA/ $\overline{\text{LIR}}$
2	PA6/OC2/OC1	26	STRA/AS
3	PA5/OC3/OC1	27	E
4	PA4/OC4/OC1	28	STRB/R/ $\overline{\text{W}}$
5	PA3/OC5/OC1	29	EXTAL
6	PA2/IC1	30	XTAL
7	PA1/IC2	31	PC0/AD0
8	PA0/IC3	32	PC1/AD1
9	PB7/A15	33	PC2/AD2
10	PB6/A14	34	PC3/AD3
11	PB5/A13	35	PC4/AD4
12	PB4/A12	36	PC5/AD5
13	PB3/A11	37	PC6/AD6
14	PB2/A10	38	PC7/AD7
15	PB1/A9	39	$\overline{\text{RESET}}$
16	PB0/A8	40	$\overline{\text{XIRQ}}$
17	PE0/AN0	41	$\overline{\text{IRQ}}$
18	PE1/AN1	42	PD0/RxD
19	PE2/AN2	43	PD1/TxD
20	PE3/AN3	44	PD2/MISO
21	V_{RL}	45	PD3/MOSI
22	V_{RH}	46	PD4/SCK
23	V_{SS}	47	PD5/ $\overline{\text{SS}}$
24	MODB/V_{stby}	48	V_{DD}

FIGURE 2. Terminal connections.

Device type	01		
Case outline	Y		
Terminal number	Terminal symbol	Terminal number	Terminal symbol
1	XTAL	27	PA0/IC3
2	PC0/AD0	28	PB7/A15
3	PC1/AD1	29	PB6/A14
4	PC2/AD2	30	PB5/A13
5	PC3/AD3	31	PB4/A12
6	PC4/AD4	32	PB3/A11
7	PC5/AD5	33	PB2/A10
8	PC6/AD6	34	PB1/A9
9	PC7/AD7	35	PB0/A8
10	$\overline{\text{RESET}}$	36	PE0/AN0
11	$\overline{\text{XIRQ}}$	37	PE4/AN4
12	$\overline{\text{IRQ}}$	38	PE1/AN1
13	PD0/RxD	39	PE5/AN5
14	PD1/TxD	40	PE2/AN2
15	PD2/MISO	41	PE6/AN6
16	PD3/MOSI	42	PE3/AN3
17	PD4/SCK	43	PE7/AN7
18	PD5/ $\overline{\text{SS}}$	44	V_{RL}
19	V_{DD}	45	V_{RH}
20	PA7/PAI/OC1	46	V_{SS}
21	PA6/OC2/OC1	47	MODB/V_{stby}
22	PA5/OC3/OC1	48	MODA/ $\overline{\text{LIR}}$
23	PA4/OC4/OC1	49	STRA/AS
24	PA3/OC5/OC1	50	E
25	PA2/IC1	51	STRB/R/ $\overline{\text{W}}$
26	PA1/IC2	52	EXTAL

FIGURE 2. Terminal connections - Continued.

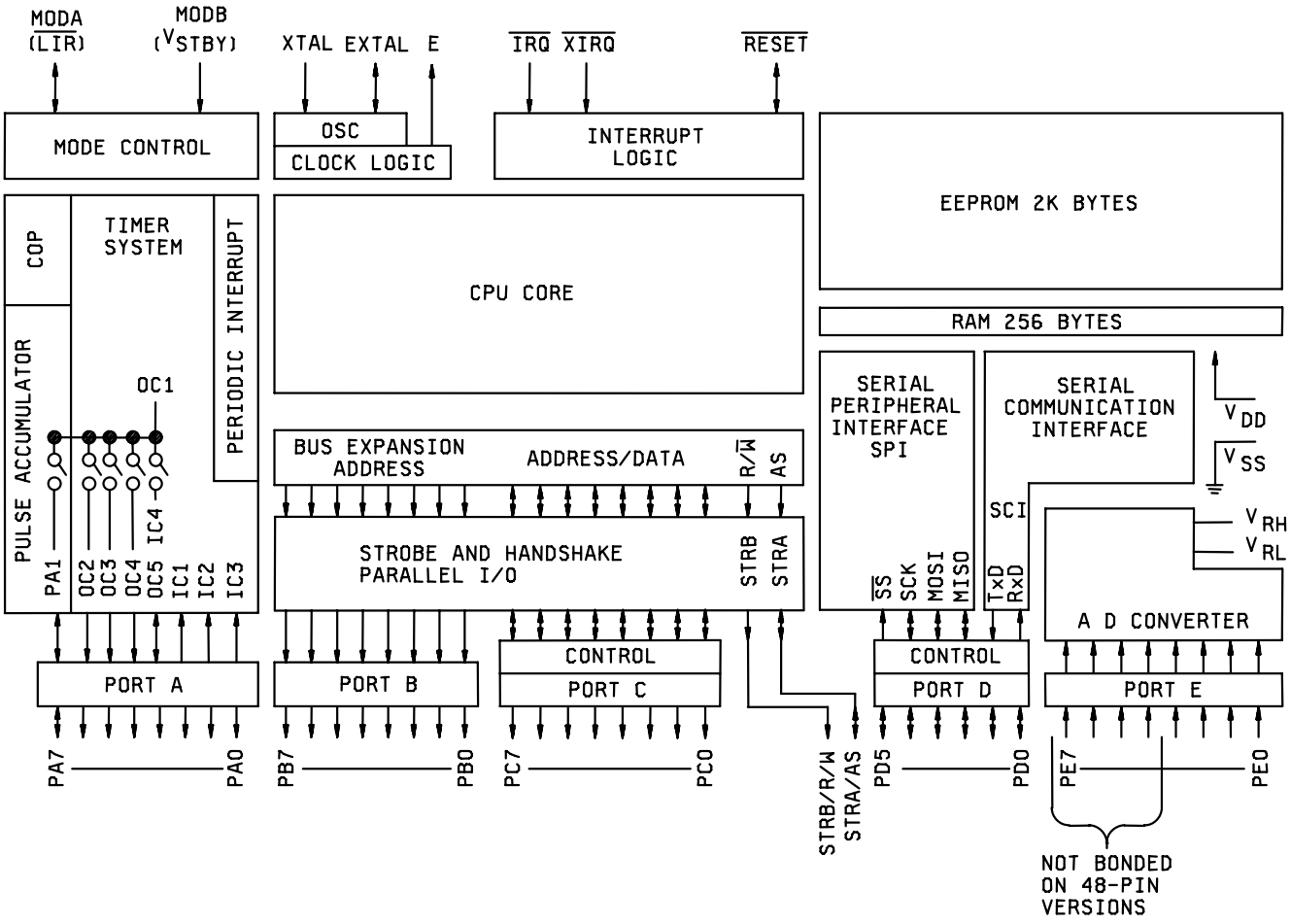
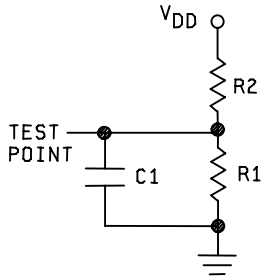


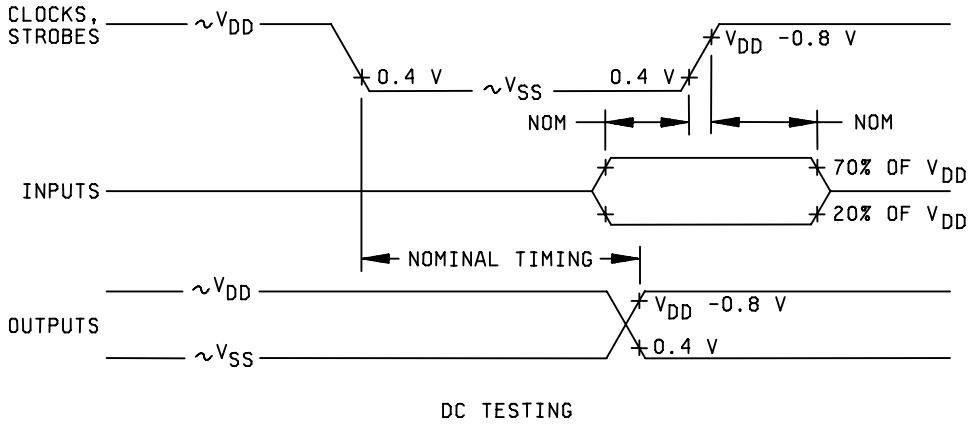
FIGURE 3. Block diagram.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43218-3990	SIZE A		5962-89527
		REVISION LEVEL C	SHEET 17

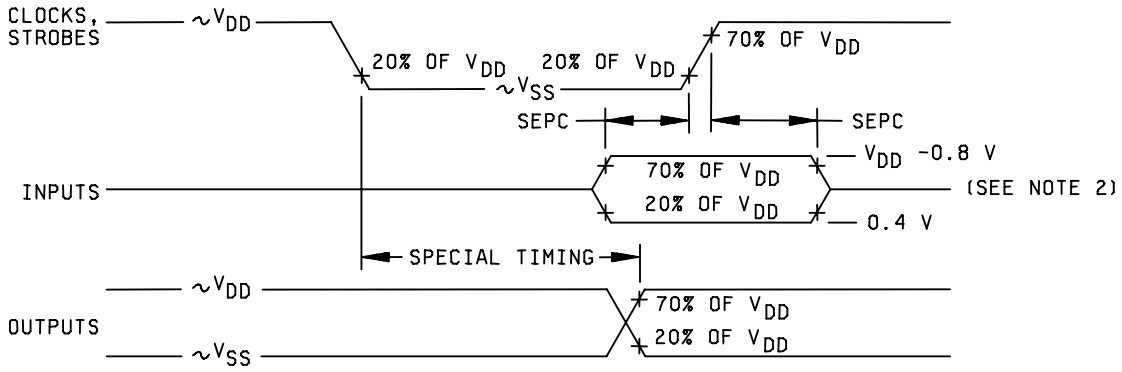


Equivalent test load

Pins	R1	R2	C1
PA3-PA7 PB0-PB7 PC0-PC7 PD0-PD5 E, AS, R/$\overline{W}$	3.26 kΩ	2.38 kΩ	90 pF
PD1-PD4	3.26 kΩ	2.38 kΩ	200 pF



DC TESTING

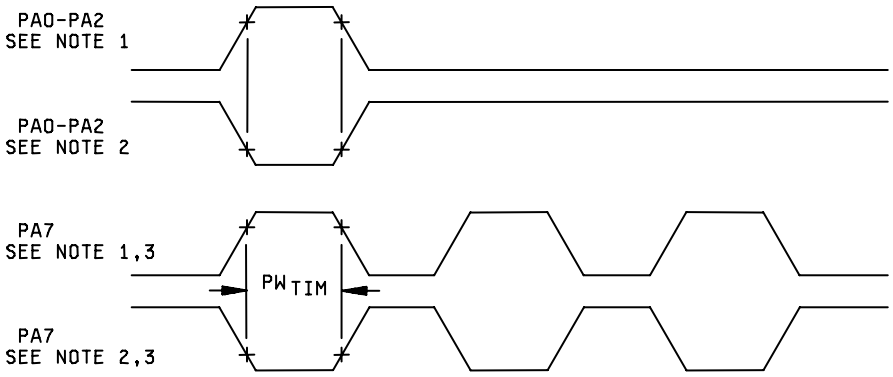


AC TESTING

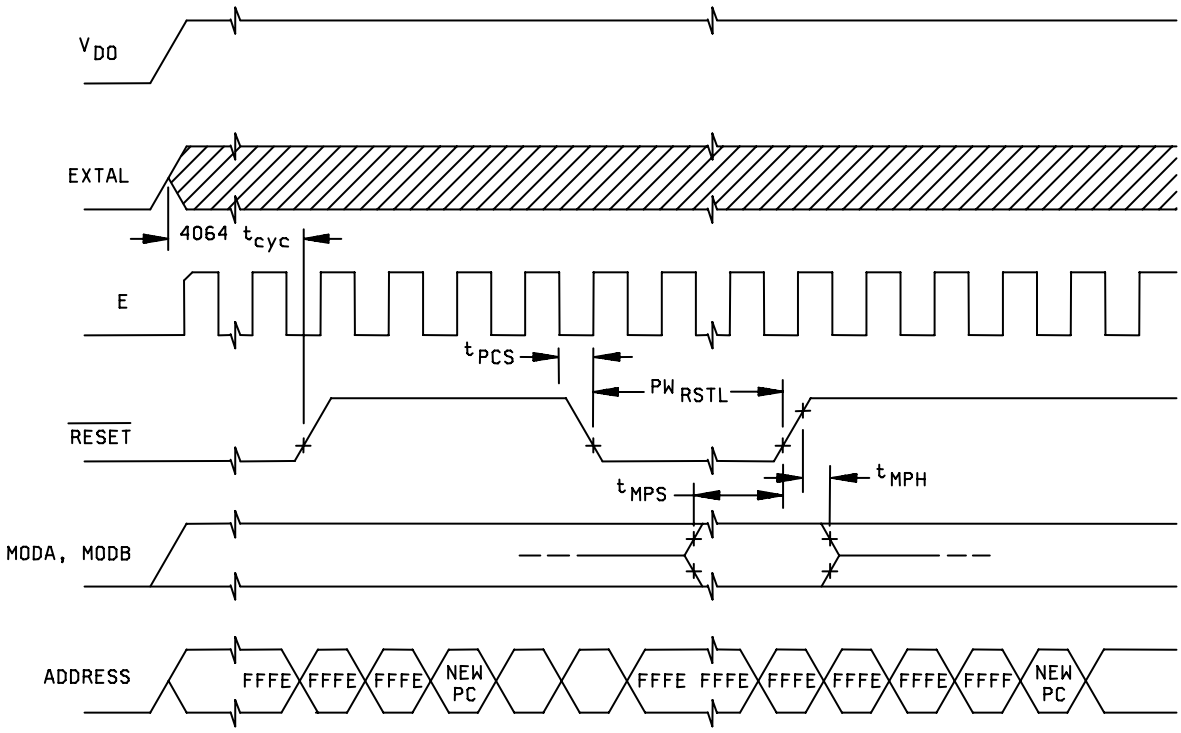
NOTES:
1. Full test loads are applied during all ac electrical test and ac timing measurements.
2. During AC timing measurements, inputs are driven to 0.4 V and V_{DD} -0.8 V while timing measurements are taken at the 20 percent and 70 percent of V_{DD} points.

FIGURE 4. Test circuit and switching waveforms.

TIMER INPUTS TIMING



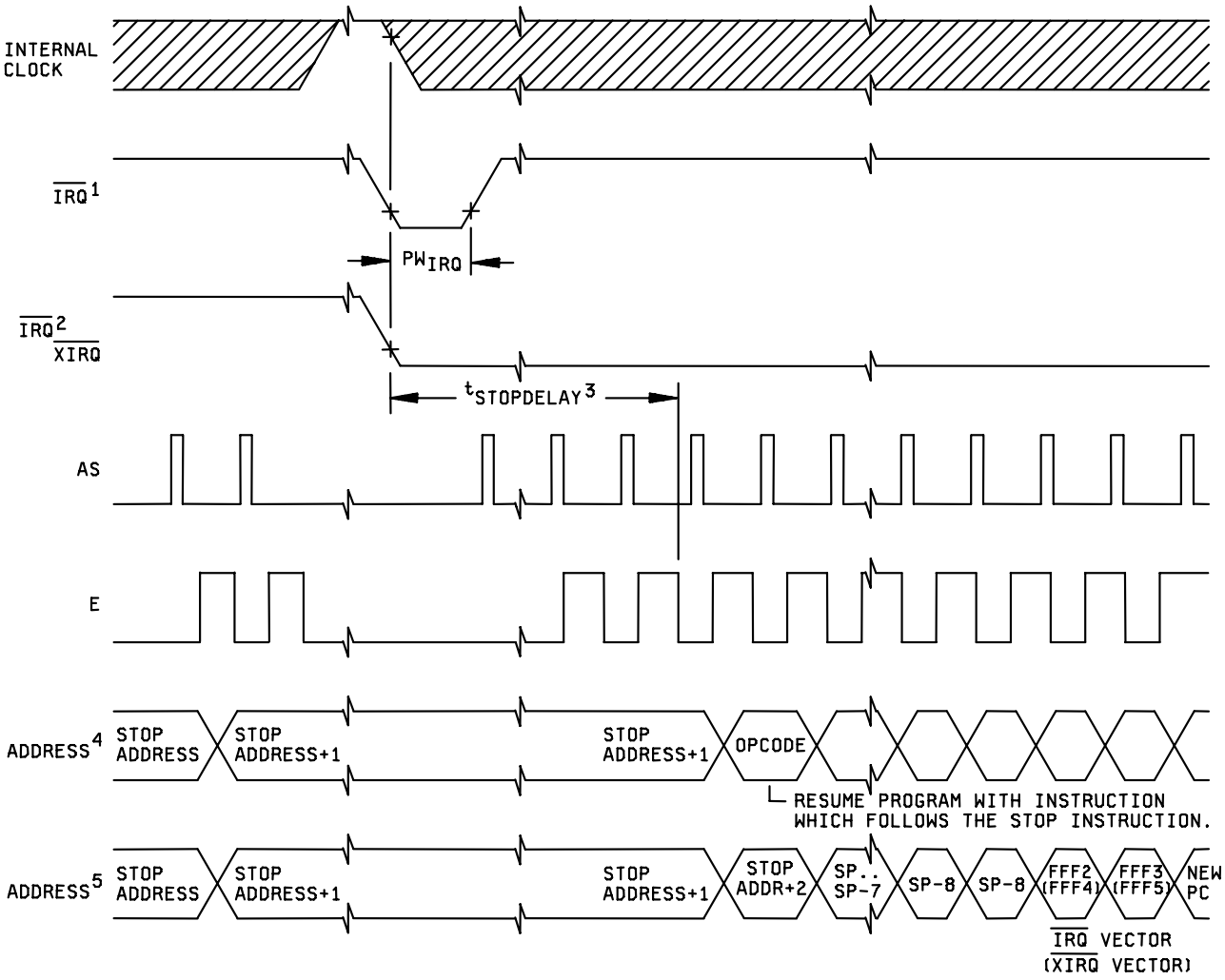
POR EXTERNAL RESET TIMING



NOTES:
1. Rising edge sensitive input.
2. Falling edge sensitive input.
3. Maximum pulse accumulator clocking rate is E frequency divided by 2.

FIGURE 4. Test circuit and switching waveforms – Continued.

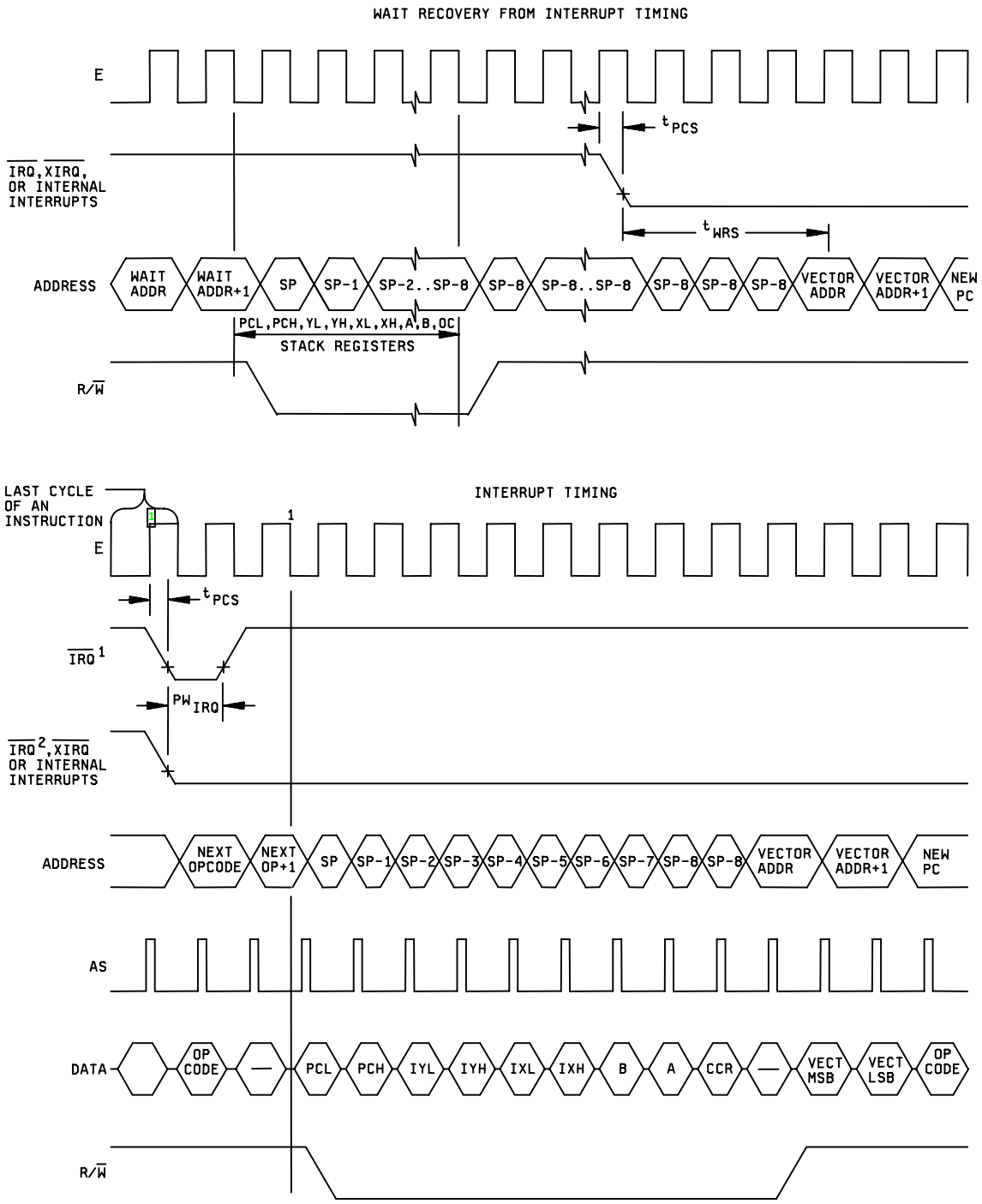
STOP RECOVERY TIMING



NOTES:

1. Edge sensitive $\overline{\text{IRQ}}$ pin (IRQE bit = 1).
2. Level sensitive $\overline{\text{IRQ}}$ pin (IRQE bit = 0).
3. $t_{STOPDELAY}$ = 4064 t_{cyc} if DLY bit = 1 or 4 t_{cyc} if DLY = 0.
4. XIQ with X bit in CCR = 1.
5. $\overline{\text{IRQ}}$ or $\overline{\text{XIRQ}}$ with X bit in CCR = 0.

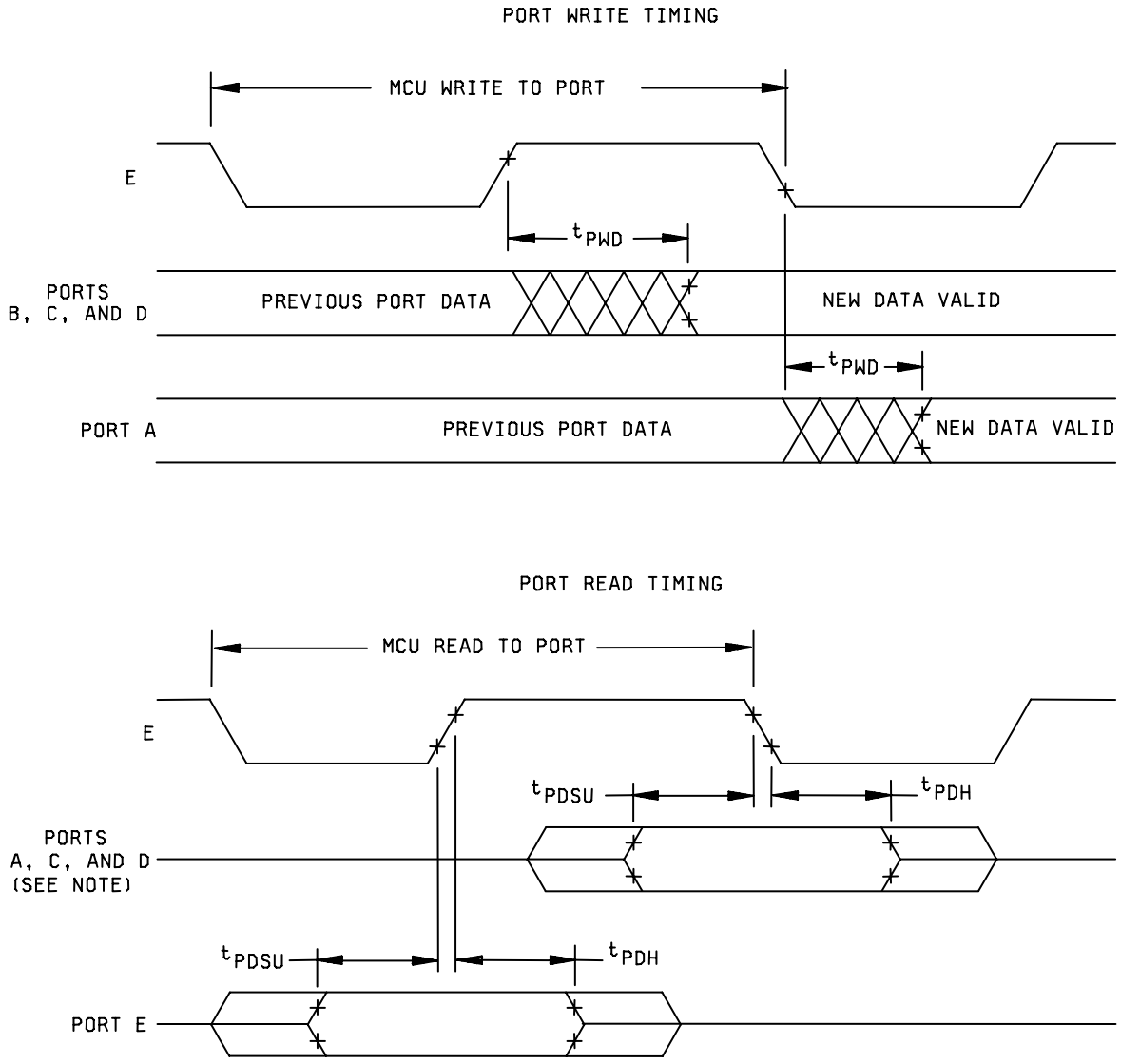
FIGURE 4. Test circuit and switching waveforms – Continued.



NOTES:

1. Edge sensitive $\overline{IRQ}$ pin (IRQE bit = 1).
2. Level sensitive $\overline{IRQ}$ pin (IRQE bit = 0).

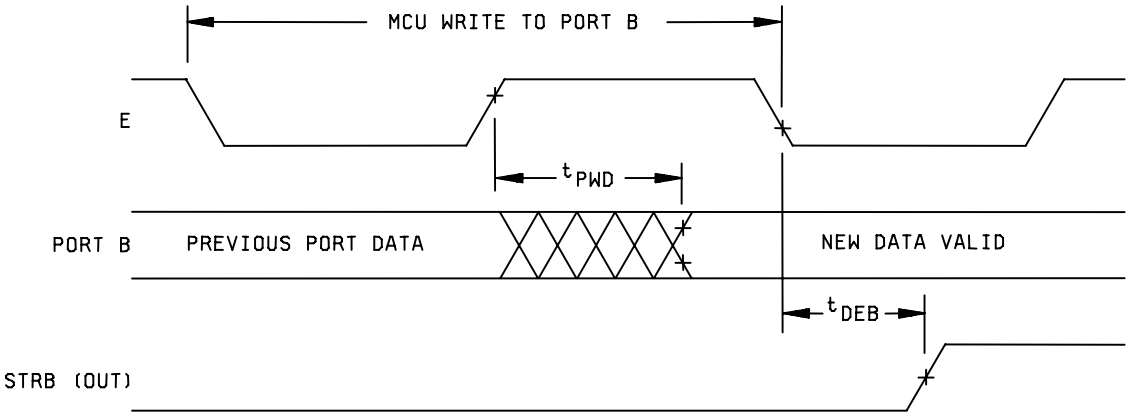
FIGURE 4. Test circuit and switching waveforms – Continued.



NOTE: For nonlatched operation of port C.

FIGURE 4. Test circuit and switching waveforms – Continued.

SIMPLE OUTPUT STROBE TIMING



SIMPLE INPUT STROBE TIMING

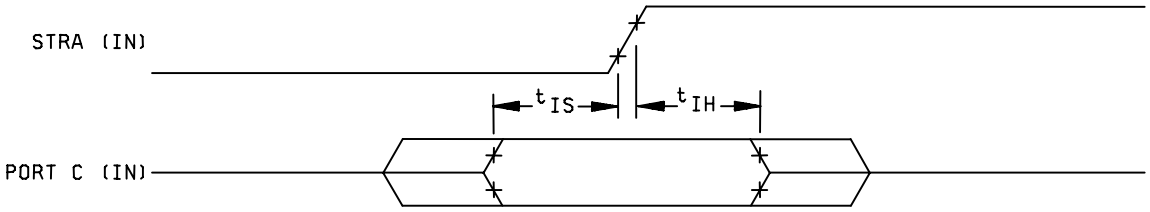
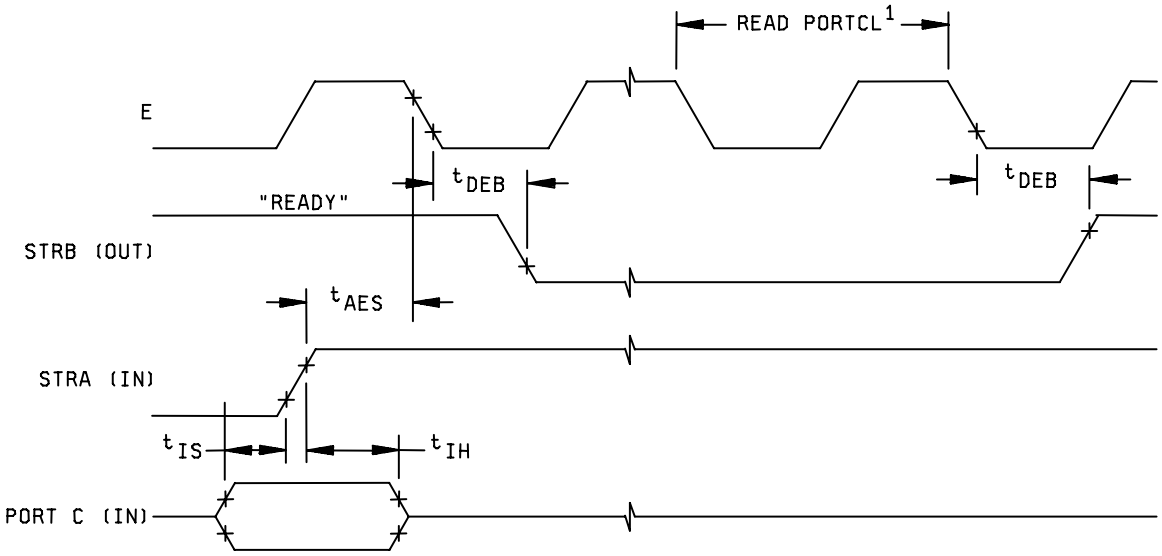
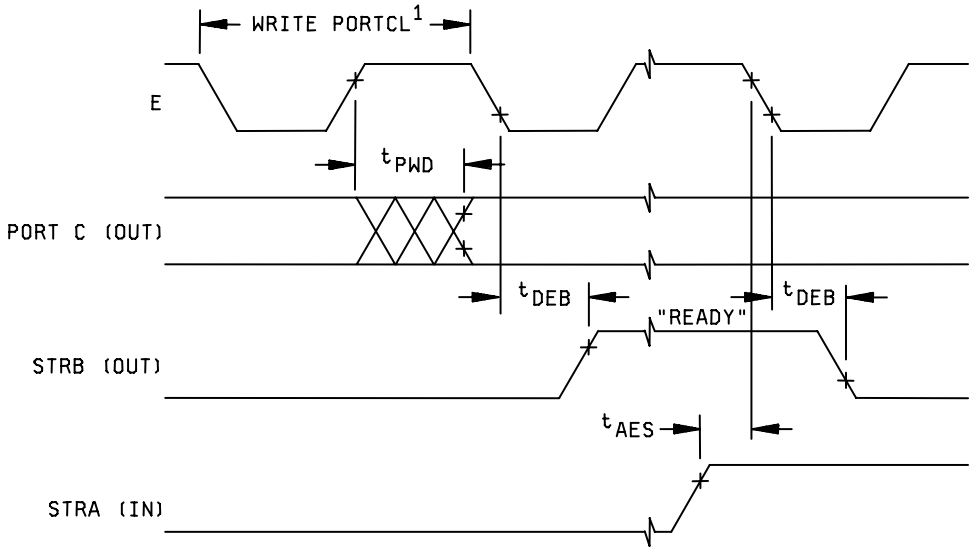


FIGURE 4. Test circuit and switching waveforms – Continued.

PORT C INPUT HANDSHAKE TIMING



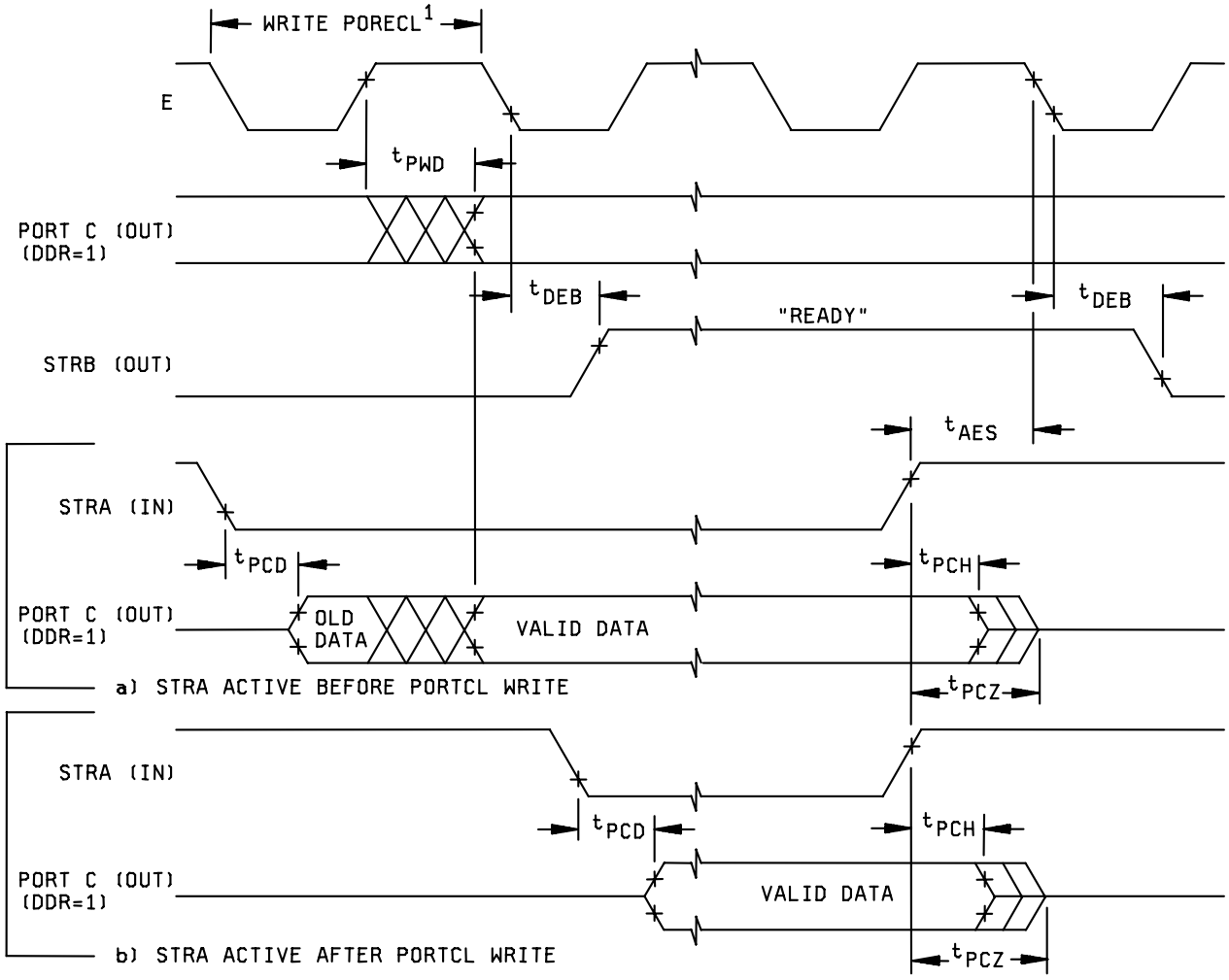
PORT C OUTPUT HANDSHAKE TIMING



NOTES:
1. After reading PIOC with STAF set.
2. Figures show rising edge STRA (EGA = 1) and high true STRB (INVB = 1).

FIGURE 4. Test circuit and switching waveforms – Continued.

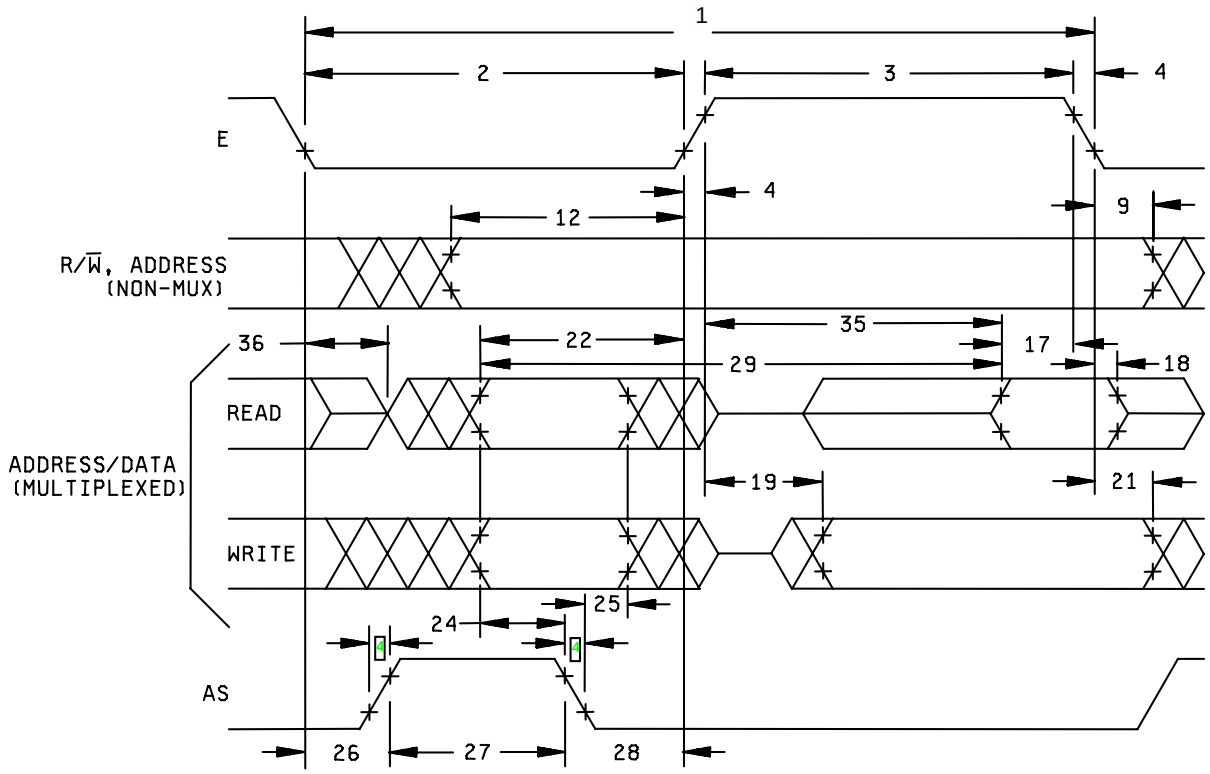
THREE-STATE VARIATION OF OUTPUT HANDSHAKE TIMING
(STRA ENABLES OUTPUT BUFFER)



NOTES:
1. After reading PIOC with STAF set.
2. Figures show rising edge STRA (EGA = 1) and high true STRB (INVB = 1).

FIGURE 4. Test circuit and switching waveforms – Continued.

EXPANSION BUS TIMING

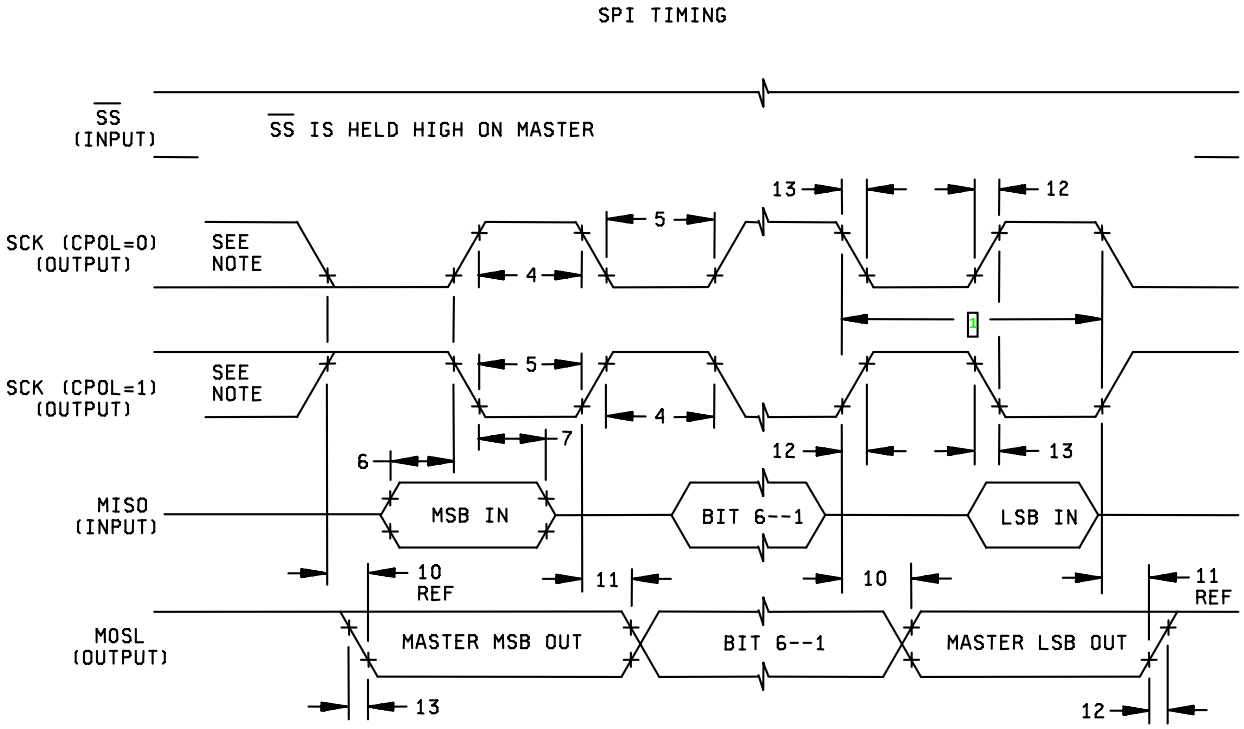


NOTE: Measurement points shown are 20 percent and 70 percent V_{DD}.

Waveform number references.

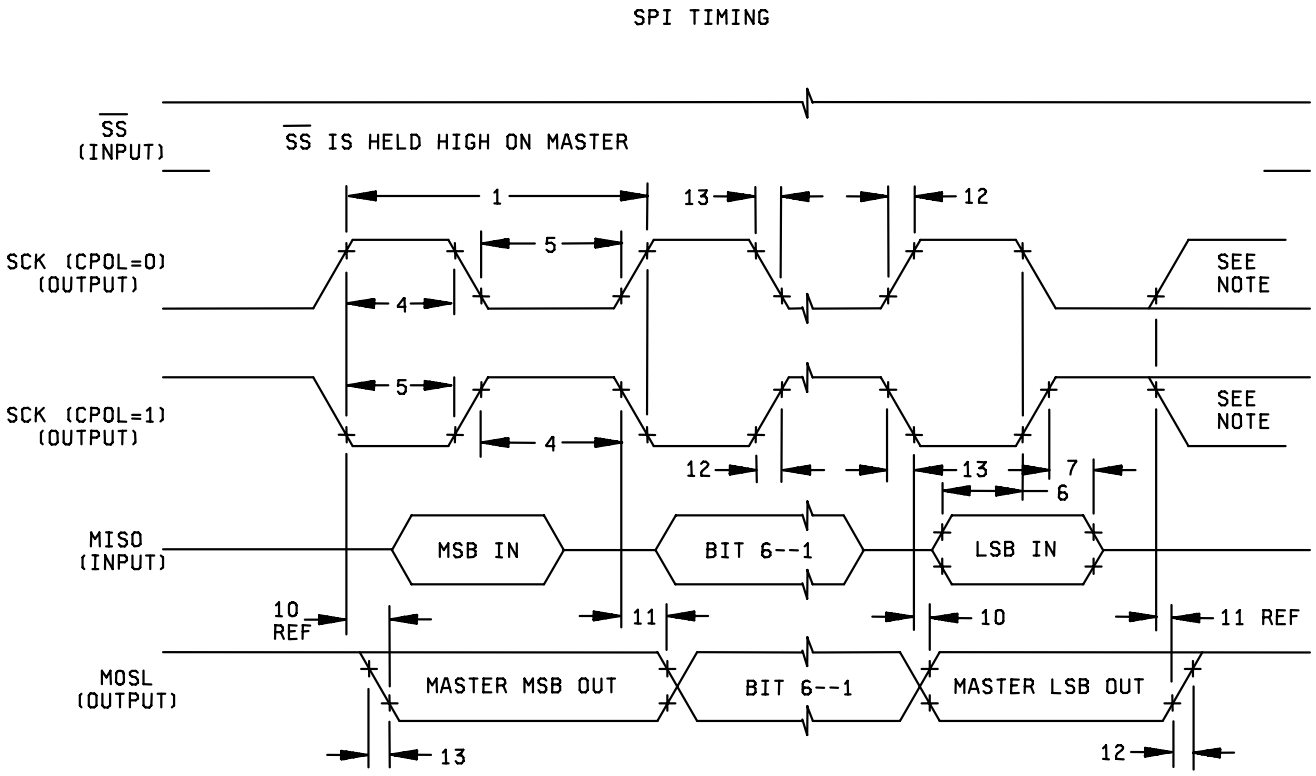
Number	Symbol	Number	Symbol	Number	Symbol	Number	Symbol
1	t_{cyc}	2	PW_{EL}	3	PW_{EH}	4	t_r, t_f
9	t_{AH}	12	t_{AV}	17	t_{DSR}	18	t_{DHR}
19	t_{DDW}	21	t_{DHW}	22	t_{AVM}	24	t_{ASL}
25	t_{AHL}	26	t_{ASD}	27	PW_{ASH}	28	t_{ASED}
29	t_{ACCA}	35	t_{ACCE}	36	t_{MAD}		

FIGURE 4. Test circuit and switching waveforms – Continued.



NOTE: This first clock edge is generated internally but is not seen at the SCK pin. SPI MASTER TIMIMG (CPHA = 0).

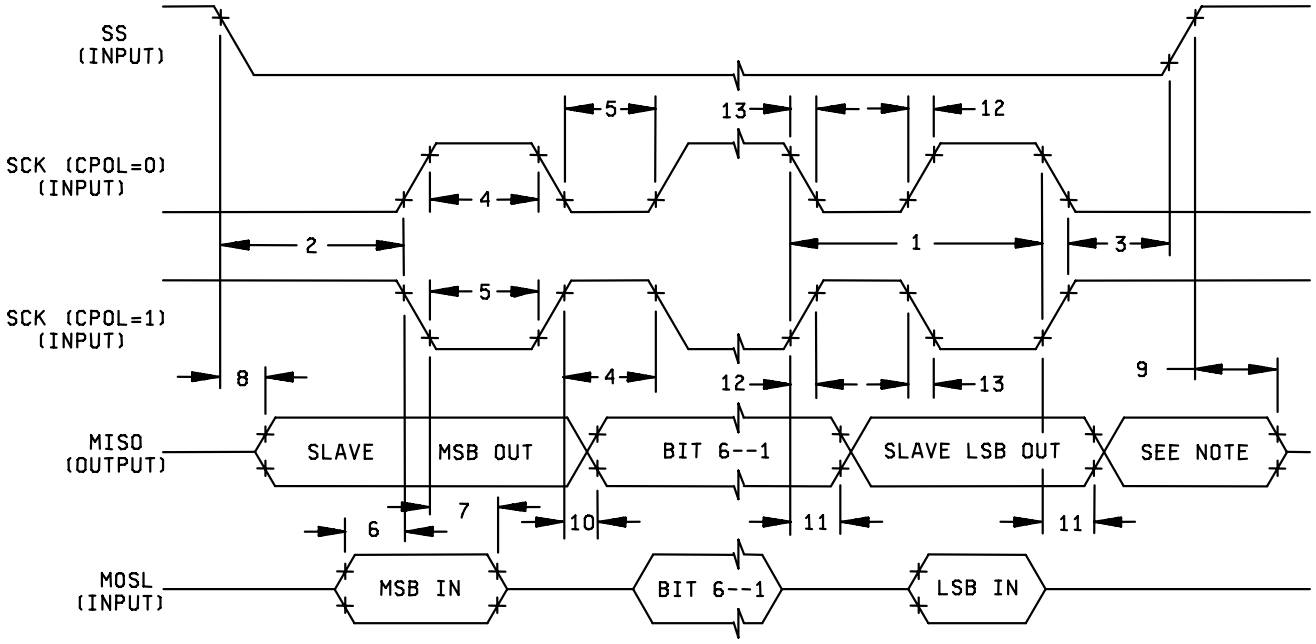
FIGURE 4. Test circuit and switching waveforms – Continued.



NOTE: This last clock edge is generated internally but is not seen at the SCK pin. SPI MASTER TIMIMG (CPHA = 0).

FIGURE 4. Test circuit and switching waveforms – Continued.

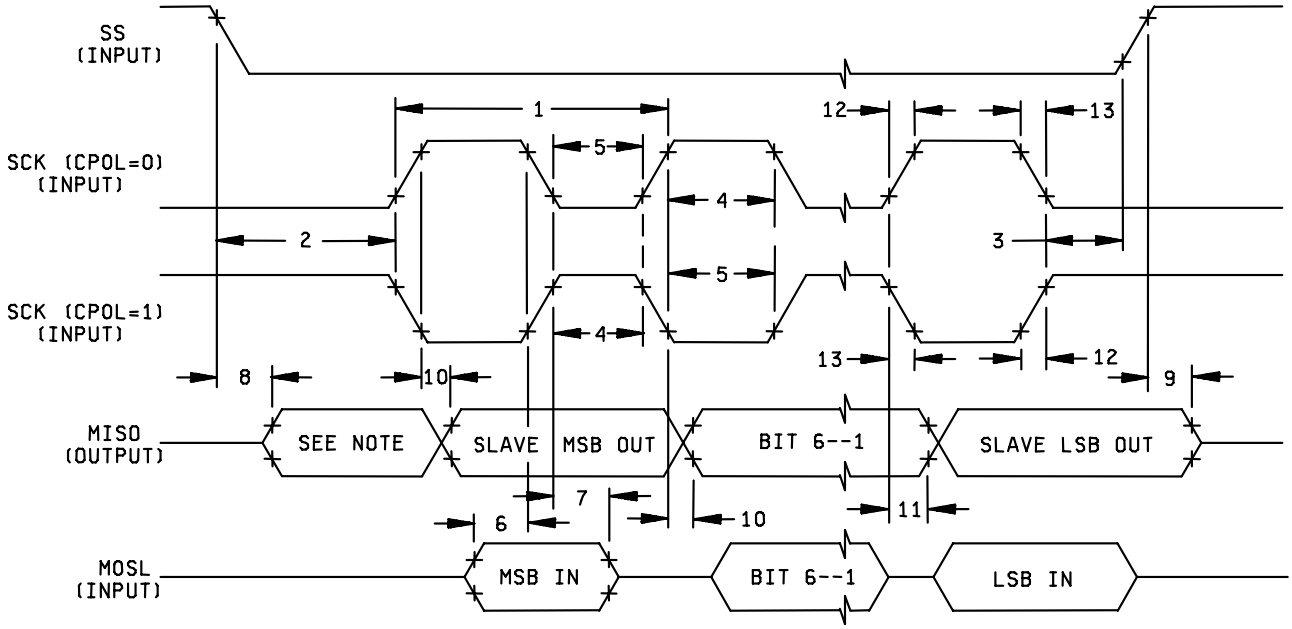
SPI TIMING



NOTE: Not defined but normally MSB of character just received. SPI SLAVE TIMING (CPHA = 0).

FIGURE 4. Test circuit and switching waveforms – Continued.

SPI TIMING



NOTE: Not defined but normally LSB of character previously transmitted. SPI SLAVE TIMING (CPHA = 0).

Waveform number references - SPI timing.

Number	Symbol	Master/slave	Number	Symbol	Master/slave
1	t_{cyc}	m,s	2	t_{lead}	m,s
3	t_{lag}	m,s	4	$t_{w(SCKH)}$	m,s
5	$t_{w(SCKL)}$	m,s	6	t_{su}	m,s
7	t_h	m,s	8	t_a	
9	t_{dis}		10	t_v	s
11	t_{ho}		12	t_r	m,s
13	t_f	m,s			

FIGURE 4. Test circuit and switching waveforms – Continued.

4. VERIFICATION

4.1 Sampling and inspection. Sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.

4.2 Screening. Screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. The following additional criteria shall apply:

a. Burn-in test, method 1015 of MIL-STD-883.

(1) Test condition A or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.

(2) T_A = +125°C, minimum.

b. Interim and final electrical test parameters shall be as specified in table II herein, except interim electrical parameter tests prior to burn-in are optional at the discretion of the manufacturer.

c. An endurance/data retention test prior to burn-in, in accordance with method 1033 of MIL-STD-883, shall be included as part of the screening procedure with the following conditions:

(1) Cycling may be block, byte, or page at +125°C and shall cycle all bytes for a minimum of 1000 cycles and the devices shall remain at +125°C for 24 hours.

(2) After cycling, perform a high temperature unbiased bake for 72 hours at 150°C (minimum). The storage time may be accelerated by using higher temperature in accordance with the Arrhenius Relationship:

$A_F = \exp(-E_A/K*(1/T1 - 1/T2))$ where:

A_F = acceleration factor (unitless quantity) = t_1/t_2
T = temperature in Kelvin
t_1 = time (hrs) at temperature T1
t_2 = time (hrs)
K = Boltzmann's constant = 8.62×10^{-5}eV/°K using an apparent activation energy (E_A) of 0.6 V.

The maximum storage temperature shall not exceed 200°C for packaged devices or 300°C for unassembled devices.

(3) Read the data retention pattern and test using subgroups 1, 7, and 9 (minimum, e.g., high temperature equivalent subgroups 2, 8A, and 10 may be used) after cycling and bake, prior to burn-in. Devices having bits not in the proper state after storage shall constitute a device failure.

4.3 Quality conformance inspection. Quality conformance inspection shall be in accordance with method 5005 of MIL-STD-883 including groups A, B, C, and D inspections. The following additional criteria shall apply.

4.3.1 Group A inspection.

a. Tests shall be as specified in table II herein.

b. Subgroup 4 (C_{IN} measurement) shall be measured only for the initial test and after process or design changes which may affect input capacitance. A minimum sample size of five devices with zero rejects shall be required.

c. All devices selected for testing shall have the EEPROM programmed with a checkerboard pattern or equivalent. After completion of all testing, the devices shall be erased and verified (except devices submitted for groups C and D testing).

d. Subgroups 7 and 8 shall consist of verifying the EEPROM pattern specified and the instruction set. The instruction set forms a part of the vendor's test tape and shall be maintained and available from the approved source of supply upon request.

TABLE II. Electrical test requirements.

MIL-STD-883 test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)
Interim electrical parameters (method 5004)	1, 7, 9
Final electrical test parameters (method 5004)	1*, 2, 3, 5, 6, 7, 8A, 9, 10, 11
Group A test requirements (method 5005)	1*, 2, 3, 4, 5, 6, 7, 8A, 9, 10, 11
Groups C and D end-point electrical parameters (method 5005)	1, 2, 3
Additional electrical subgroups for group C periodic inspections	---

* PDA applies to subgroup 1.

4.3.2 Groups C and D inspections.

a. End-point electrical parameters shall be as specified in table II herein.

b. All devices requiring end-point electrical testing shall be programmed with a checkerboard or equivalent alternating bit pattern.

c. Steady-state life test conditions, method 1005 of MIL-STD-883.

(1) Test condition A or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.

(2) T_A = +125°C, minimum.

(3) Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

d. An endurance test, in accordance with method 1033 of MIL-STD-883, shall be added to group C1 inspection prior to performing the steady-state life test (see 4.3.2c) and extended data retention (see 4.3.2e).

Cycling may be block, byte, or page from devices passing group A after the completion of the requirements of 4.2 herein.

(1) All bytes shall be cycled for a minimum of 4,000 cycles at +25°C.

(2) Perform group A subgroups 1 and 7.

e. Extended data retention shall consist of:

(1) All devices shall be programmed with a charge on all memory cells in each device, such that the cell will read opposite the state that the cell would read in its equilibrium state (e.g., worst case pattern, see 4.2c(2)).

(2) Perform a high temperature unbiased bake for 1000 hours at 150°C (minimum). The storage time may be accelerated by using higher temperature in accordance with the Arrhenius Relationship:

$A_F = \exp(-E_A/K*(1/T1 - 1/T2))$ where:

A_F = acceleration factor (unitless quantity) = t_1/t_2
T = temperature in Kelvin
t_1 = time (hrs) at temperature T1
t_2 = time (hrs)
K = Boltzmann's constant = 8.62×10^{-5}eV/°K using an apparent activation energy (E_A) of 0.6 V.

The maximum storage temperature shall not exceed 200°C for packaged devices or 300°C for unassembled devices.

(3) Read the pattern after bake and perform endpoint electrical tests for table II herein for group C.

4.4 Programming procedures. The programming procedures shall be as specified by the device manufacturer and shall be made available to the user upon request.

4.5 Erasing procedures. The erasing procedures shall be as specified by the device manufacturer and shall be made available to the user upon request.

5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-PRF-38535, appendix A.

6. NOTES

6.1 Intended use. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.2 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.

6.3 Configuration control of SMD's. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.

6.4 Record of users. Military and industrial users shall inform Defense Supply Center Columbus (DSCC) when a system application requires configuration control and the applicable SMD. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronics devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0544.

6.5 Comments. Comments on this drawing should be directed to DSCC-VA, Columbus, Ohio 43218-3990, or telephone (614) 692-0547.

6.6 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535, MIL-HDBK-1331, and table III herein.

6.7 Approved sources of supply. Approved sources of supply are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DSCC-VA.

TABLE III. Pin descriptions.

<table>
<tr><th>Pin name</th><th>Description</th></tr>
<tr><td>$\overline{\text{RESET}}$</td><td>Reset: This active low bidirectional control pin is used as an input to initialize the MCU to a known startup state and as an open-drain output to indicate that an internal failure has been detected in either the clock monitor or the computer operating properly (COP) circuit.</td></tr>
<tr><td>XTAL, EXTAL</td><td>Crystal driver and external clock input: These pins provide the interface for either a crystal or a CMOS-compatible clock to control the internal clock generator circuitry. The frequency applied shall be four times higher than the desired clock rate.</td></tr>
<tr><td>E</td><td>E clock output: This pin provides an output for the internally generated E clock which can be used for timing reference. The frequency of the E output is one fourth that of the input frequency at the XTAL and EXTAL pins.</td></tr>
<tr><td>$\overline{\text{IRQ}}$</td><td>Interrupt request: This pin provides the capability for asynchronously applying interrupts to the MCU. Either negative edge-sensitive or level-sensitive triggering is program selectable. This pin is configured to level-sensitive during reset. An external resistor connected V_{DD} is required on $\overline{\text{IRQ}}$.</td></tr>
<tr><td>$\overline{\text{XIRQ}}$</td><td>Non-maskable interrupt: This pin provides the capability for asynchronously applying non-maskable interrupts to the MCU after a power on reset (POR). During reset, the X bit in the condition code register is set, and any interrupt is masked until enabled by software. This input is level-sensitive and requires an external pullup resistor to V_{DD}.</td></tr>
<tr><td>MODA/$\overline{\text{LIR}}$ and MODB/V_{stby}</td><td>During reset, these pins are used to control the two basic operating modes and the two special operating modes. The $\overline{\text{LIR}}$ output can be used as an aid in debugging once reset is completed. The open-drain $\overline{\text{LIR}}$ pin goes to an active low during the first E-clock cycle of each instruction and remains low for the duration of that cycle. The V_{stby} (voltage standby) is used to retain RAM contents during device powerdown. The mode selections are shown below.
<table>
<tr><th>MODB</th><th>MODA</th><th>Mode selected</th></tr>
<tr><td>1</td><td>0</td><td>Single chip</td></tr>
<tr><td>1</td><td>1</td><td>Expanded multiplexed</td></tr>
<tr><td>0</td><td>0</td><td>Special bootstrap</td></tr>
<tr><td>0</td><td>1</td><td>Special test</td></tr>
</table>
</td></tr>
<tr><td>V_{RL},V_{RH}</td><td>A/D converter reference voltage: These pins provide the reference voltage for the A/D converter.</td></tr>
<tr><td>V_{SS}</td><td>GND</td></tr>
</table>

STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 08-01-09

Approved sources of supply for SMD 5962-89527 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This information bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535. DSCC maintains an online database of all current sources of sypply at http://www.dscc.dla.mil/Programs/Smcr/ .

Standard microcircuit drawing PIN 1/	Vendor CAGE number	Vendor similar PIN 2/
5962-8952701XA	F8385	TS68HC811E2MC1B/C
5962-8952701XC	F8385	TS68HC811E2MCB/C
5962-8952701YA	F8385	TS68HC811E2MF1B/C
5962-8952701YC	F8385	TS68HC811E2MFB/C
5962-8952701YC	0EU86	AS68HC811E2Q52/883C

1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.

2/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGE number	Vendor name and address
0EU86	Austin Semiconductor, Inc. 8701 Cross Park Drive Austin, TX 78754-4566
F8385	E2V Semiconductors Avenue De Rochepleine BP 123 Saint Egreve CEDEX 38521, France